

MA75WA

Silicon epitaxial planer type

For band switching

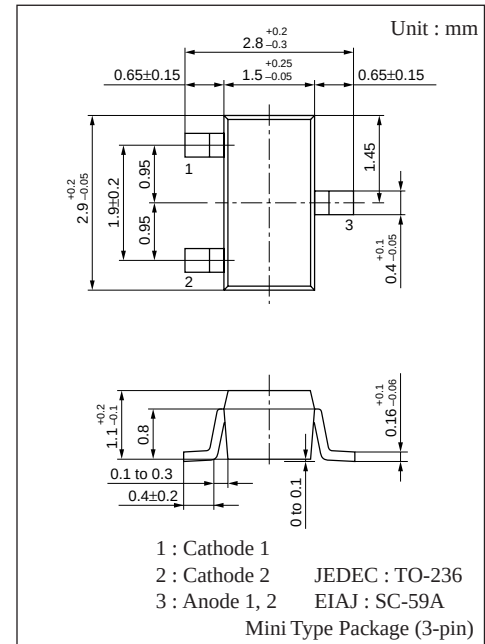
■ Features

- Low forward dynamic resistance r_f
- Less voltage dependence of diode capacity C_D
- Mini package, enabling down-sizing of the equipment and automatic insertion through taping

■ Absolute Maximum Ratings (Ta= 25°C)

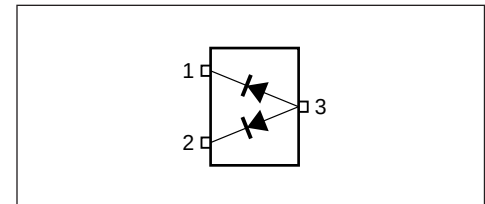
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	35	V
Forward current (DC)	I_F	100	mA
Operating ambient temperature	T_{opr}^*	- 25 to + 85	°C
Storage temperature	T_{stg}	- 55 to +150	°C

* Maximum ambient temperature during operation



Marking Symbol : M1X

■ Internal Connection



■ Electrical Characteristics (Ta= 25°C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R = 33V$		0.01	100	nA
Forward voltage (DC)	V_F	$I_F = 100mA$		0.92	1.0	V
Diode capacitance	C_D	$V_R = 6V, f = 1MHz$		0.9	1.2	pF
Forward dynamic resistance	r_f^*	$I_F = 2mA, f = 100MHz$		0.65	0.85	Ω

Note 1 : Each characteristic is a standard for individual diodes

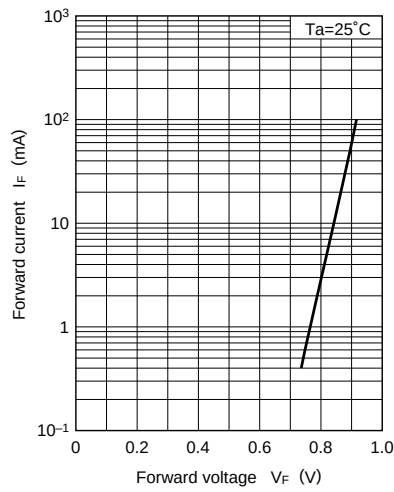
2 : Rated input/output frequency : 100MHz

3 : * r_f measurement device : YHP MODEL 4191A RF IMPEDANCE ANALYZER

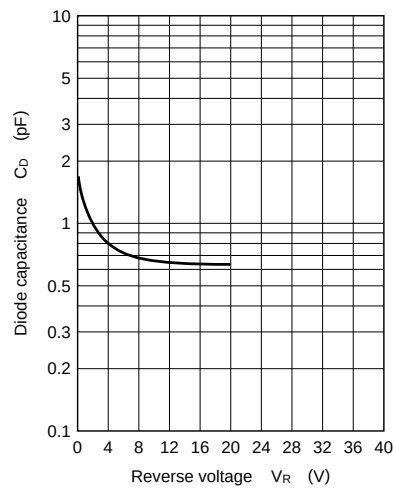
■ Marking



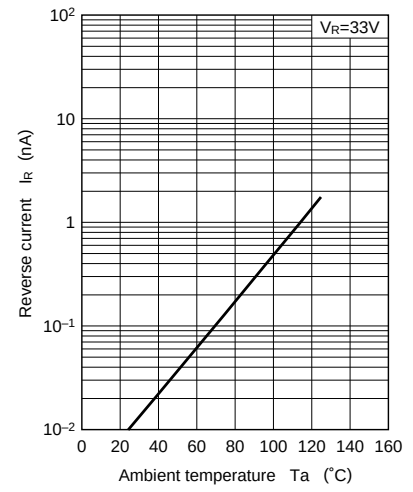
$I_F - V_F$



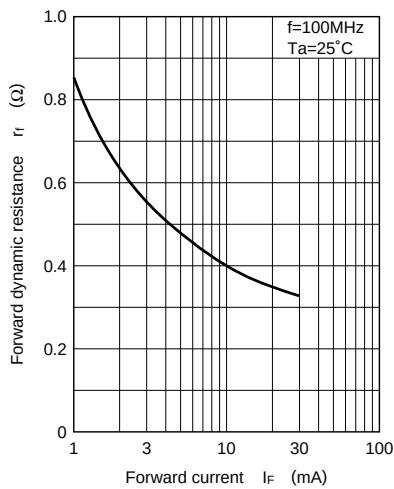
$C_D - V_R$



$I_R - T_a$



$r_f - I_F$



$r_f - f$

